

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A semiconductor device on which an insulated gate bipolar transistor and a control circuit for driving the insulated gate bipolar transistor are formed on a same semiconductor substrate, comprising:

an input terminal via which a drive signal of the insulated gate bipolar transistor is input;

a Schottky barrier diode having an anode connected to the input terminal and a cathode connected to an input terminal of the control circuit; and

a first p-channel MOSFET that shorts both ends of the Schottky barrier diode when the voltage of the drive signal input to the input terminal is higher than a predetermined voltage.

Claim 2 (Original): The semiconductor device according to claim 1, further comprising a resistor which is interposed between the cathode of the Schottky barrier diode and the input terminal of the control circuit.

Claim 3 (Currently Amended): The semiconductor device according to claim 1, further comprising a second p-channel MOSFET which is serially connected between the cathode of the Schottky barrier diode and the input terminal of the control circuit.

Claim 4 (Currently Amended): The semiconductor device according to claim 1, wherein a series circuit of a resistor and a second p-channel MOSFET is connected between the gate and the emitter of the insulated gate bipolar transistor.

Claim 5 (Currently Amended): The semiconductor device according to claim 1, further comprising a CMOS inverter circuit having an output terminal connected to the gate

of the first p-channel MOSFET, wherein a signal depending on a signal level of the drive signal input via the input terminal is input to the input terminal of the CMOS inverter circuit.